



东莞华远电子有限公司

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TO-92 Plastic-Encapsulate Transistors

2SC3279

TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.75 W ($T_{amb}=25$)

Collector current

I_{CM} : 2 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J , T_{stg} : -55 to +150

TO—92

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

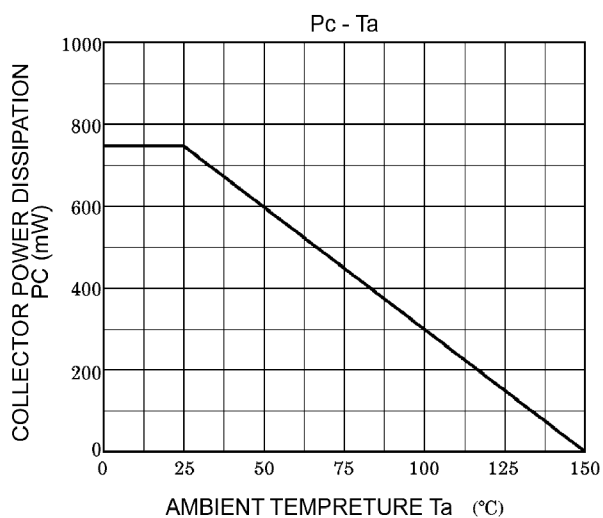
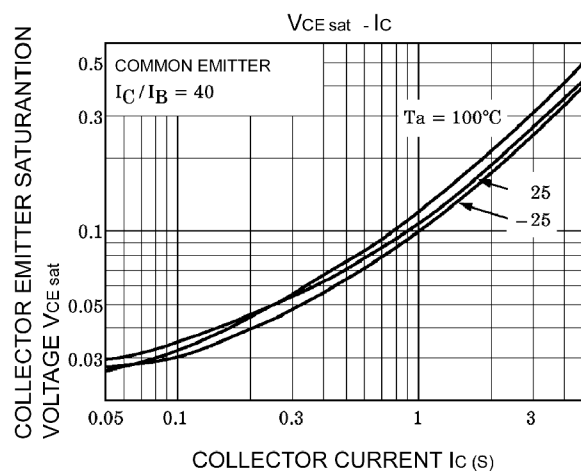
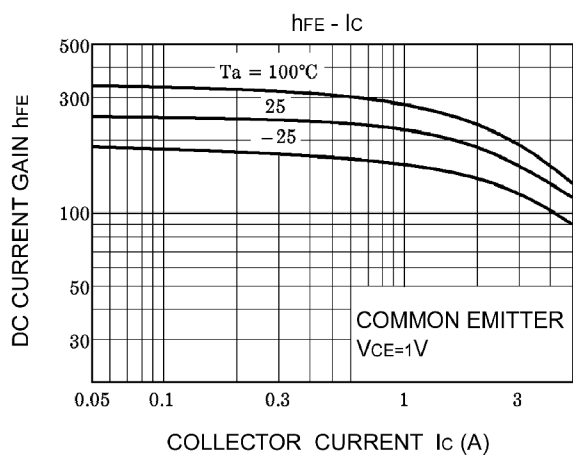
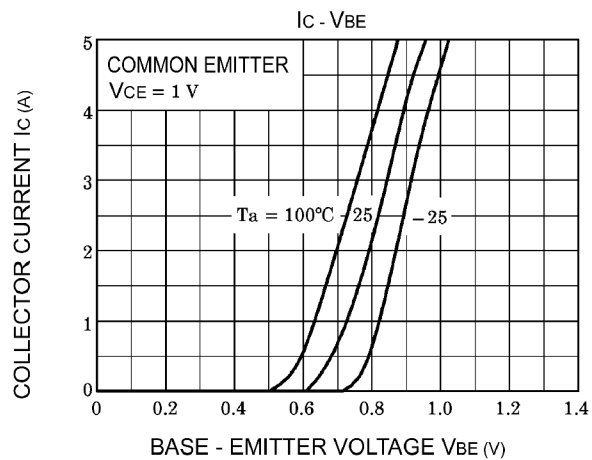
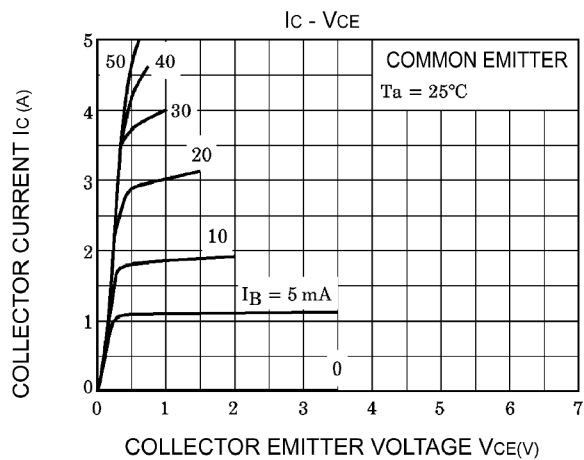
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA$, $I_E=0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA$, $I_B=0$	10		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA$, $I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V$, $I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V$, $I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V$, $I_C=0.5A$	140	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A$, $I_B=100mA$		0.5	V
Base-emitter voltage	V_{BE}	$I_C=2A$, $V_{CE}=1V$		1.5	V
Transition frequency	f_T	$V_{CE}=1V$, $I_C=0.5A$ $f=30MHz$	100		MHz

CLASSIFICATION OF h_{FE}

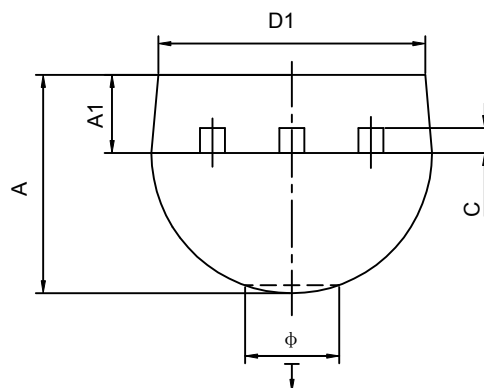
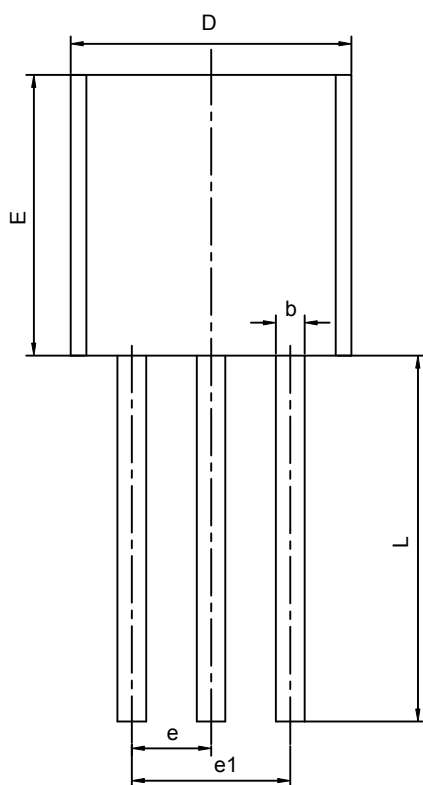
Rank	L	M	N	P
Range	140-240	200-330	300-450	420-600

Typical Characteristics

2SC3279



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
↓	0.000	0.380	0.000	0.015